

Symposium (Oral) | Symposium | Progress of compound semiconductor device technologies: what can learn from history of GaAs device development

## [17p-E201-1~7]Progress of compound semiconductor device technologies: what can learn from history of GaAs device development

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Sat. Mar 17, 2018 1:15 PM - 4:20 PM E201 (57-201)

△：奨励賞エントリー

▲：英語発表

▼：奨励賞エントリーかつ英語発表

空欄：どちらもなし

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3:50 PM - 4:20 PM

## [17p-E201-7]Current status and perspectives of SiC power devices development

○Yoshiyuki Yonezawa<sup>1</sup> (1.AIST)

Keywords:Silicon Carbide, Power device